

### **General Description**

The WSF50P04 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF50P04 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

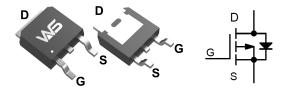
### **Product Summery**

BVDSS	RDSON	ID
-40V	12mΩ	-40A

### **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### **TO-252 Pin Configuration**



# Absolute Maximum Ratings (Tc=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage	-40	V	
Vgs	Gate-Source Voltage	±20	V	
<b>I</b> D	Drain Current-Continuous	-40	А	
l⊳ (100°C)	Drain Current-Continuous(Tc=100℃)	-28	Α	
Ірм	Pulsed Drain Current	-160	Α	
P□	Maximum Power Dissipation Tc=25°C	80	W	
Eas	Single pulse avalanche energy (Note 5)	544	mJ	
d∨/dt	Drain Source voltage slope, V <sub>DS</sub> ≤-32 V,	50	V/ns	
d∨/dt	Reverse diode dv/dt, V <sub>DS</sub> ≤-32 V, I <sub>SD</sub> <i<sub>D</i<sub>	15	V/ns	
Тл,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 175 ℃		
Rejc	Thermal Resistance,Junction-to-Case(Note 2)	1.88	°C/W	
Reja	Thermal Resistance,Junction-to-Ambient(Note 2)	50	°C/W	



## Electrical Characteristics (Tc=25°C unless otherwise noted)

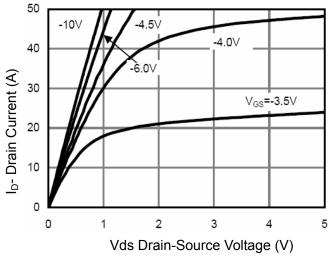
Symbol	Parameter	Condition	Min	Тур	Max	Unit
Off Character	istics					
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-40			V
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-40V,V <sub>GS</sub> =0V			-1	μΑ
Igss	Gate-Body Leakage Current	Vgs=±20V,Vps=0V			±100	nA
On Character	istics (Note 3)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1.0	-1.5	-3.0	V
RDS(ON)	Drain-Source On-State Resistance	Vgs=-10V, Ip=-12A		12	14	mΩ
		Vgs=-4.5V, ID=-12A		18.5	24	mΩ
<b>g</b> FS	Forward Transconductance	V <sub>DS</sub> =-5V,I <sub>D</sub> =-12A		34		S
Dynamic Cha	racteristics (Note4)					
Clss	Input Capacitance			2960		PF
Coss	Output Capacitance	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V, F=1.0MHz		370		PF
Crss	Reverse Transfer Capacitance			310		PF
Switching Ch	aracteristics (Note 4)					
t <sub>d(on)</sub>	Turn-on Delay Time			10		nS
tr	Turn-on Rise Time	V <sub>DD</sub> =-20V,I <sub>D</sub> =-12A V <sub>GS</sub> =-		18		nS
td(off)	Turn-Off Delay Time	10V,R <sub>G</sub> =3Ω		38		nS
tf	Turn-Off Fall Time			24		nS
Qg	Total Gate Charge			42.2	72	nC
Qgs	Gate-Source Charge	V <sub>DS</sub> =-20,I <sub>D</sub> =-12A, V <sub>GS</sub> =- 10V		6.9		nC
Qgd	Gate-Drain Charge			9.7		nC
Drain-Source	Diode Characteristics					
VsD	Diode Forward Voltage (Note 3)	V <sub>GS</sub> =0V,I <sub>S</sub> =-12A			-1.2	V
ls	Diode Forward Current (Note 2)				-40	Α
trr	Reverse Recovery Time	T <sub>J</sub> = 25°C, I <sub>F</sub> =- 12A		40		nS
Qrr	Reverse Recovery Charge	$di/dt = -100A/\mu s_{(Note3)}$		42		nC

#### Notes:

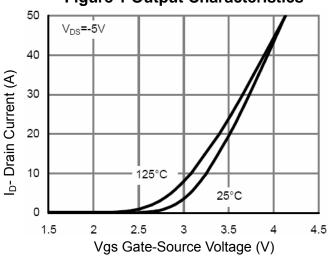
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. Eas condition: Tj=25  $^{\circ}\text{C}$  ,Vdd=-20V,Vg=-10V,L=1mH,Rg=25 $\Omega$



### **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

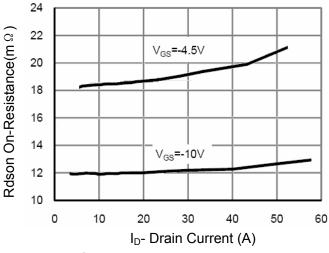
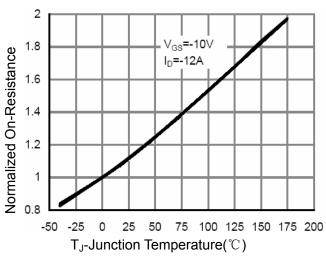


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

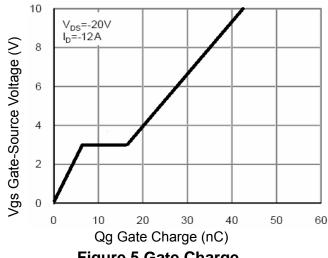


Figure 5 Gate Charge

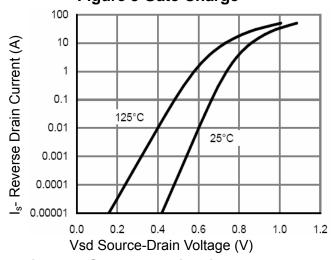


Figure 6 Source- Drain Diode Forward



P-Ch MOSFET

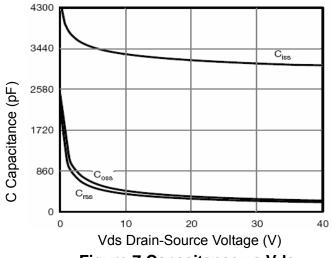
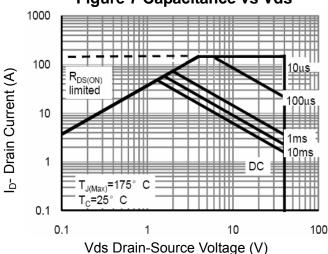


Figure 7 Capacitance vs Vds



**Figure 8 Safe Operation Area** 

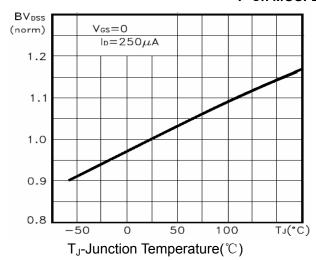


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

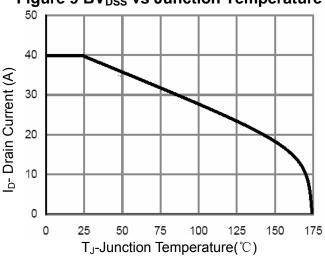
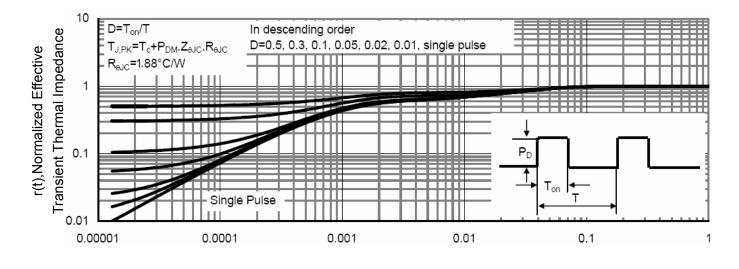


Figure 10 ID Current Derating vs Junction Temperature



**Figure 11 Normalized Maximum Transient Thermal Impedance** 

Square Wave Pluse Duration(sec)



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